

# SOT23 PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

## FMMTA56

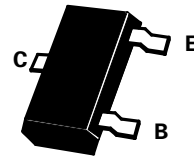
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### FEATURES

\* Gain of 50 at  $I_C=100\text{mA}$

PARTMARKING DETAIL - FMMTA56 - 2G  
FMMTA56R - MB



SOT23

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FMMTA56	UNIT
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-80	V
Emitter-Base Voltage	$V_{EBO}$	-4	V
Continuous Collector Current	$I_C$	-500	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ ).

PARAMETER	SYMBOL	FMMTA56		UNIT	CONDITIONS.
		MIN.	MAX.		
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-80		V	$I_C=-1\text{mA}, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-4		V	$I_E=-100\mu\text{A}, I_C=0$
Collector-Emitter Cut-Off Current	$I_{CES}$		-0.1	$\mu\text{A}$	$V_{CE}=-60\text{V}$
Collector-Base Cut-Off Current	$I_{CBO}$		-0.1	$\mu\text{A}$	$V_{CB}=-80\text{V}, I_E=0$ $V_{CB}=-60\text{V}, I_E=0$
Static Forward Current Transfer Ratio	$h_{FE}$	50 50			$I_C=-10\text{mA}, V_{CE}=1\text{V}^*$ $I_C=-100\text{mA}, V_{CE}=1\text{V}^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.25	V	$I_C=-100\text{mA}, I_B=-10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.2	V	$I_C=-100\text{mA}, V_{CE}=-1\text{V}^*$
Transition Frequency	$f_T$	100		MHz	$I_C=-10\text{mA}, V_{CE}=-2\text{V}$ $f=100\text{MHz}$

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

